

# XP222N03015R-G

ETR11079-001

N-channel MOSFET 20V, 0.3A

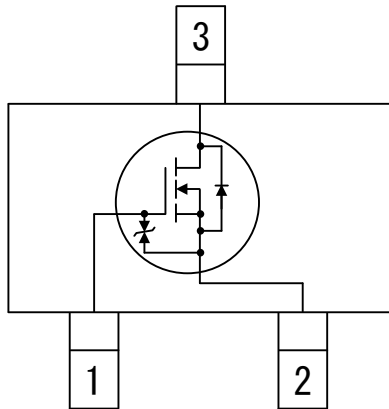
## FEATURES

**On-State Resistance** :  $R_{DS(on)}=1.3\Omega@V_{GS}=4.5V$   
**Driving voltage** : 1.8V  
**Environmentally Friendly** : EU RoHS Compliant, Pb Free

## APPLICATIONS

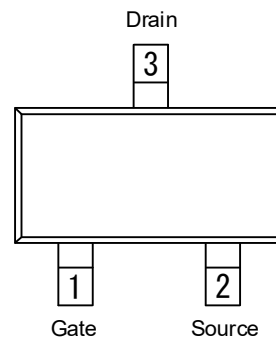
- Switching

## EQUIVALENT CIRCUIT



## PIN CONFIGURATION

- SOT-523



## PRODUCT NAME

PRODUCT NAME	PACKAGE	ORDER UNIT
XP222N03015R-G *	SOT-523	3,000 pcs/ Reel

\* The "-G" suffix denotes Halogen and Antimony free as well as being fully EU RoHS compliant

## ABSOLUTE MAXIMUM RATINGS

Ta=25°C

PARAMETER	SYMBOL	RATINGS	UNITS
Drain-Source Voltage	$V_{DSS}$	20	V
Gate-Source Voltage	$V_{GSS}$	±8	V
Drain Current (DC)	$I_D$	0.3	A
Drain Current (Pulse) <sup>(1)</sup>	$I_{DP}$	0.6	A
Channel Power Dissipation <sup>(2)</sup>	$P_d$	0.35	W
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{stg}$	-55~150	°C

<sup>(1)</sup>  $PW \leq 10\mu s, duty\ cycle \leq 1\%$

<sup>(2)</sup> When implemented on a PCB defined by JESD51-7

## ■ ELECTRICAL CHARACTERISTICS

Ta=25°C

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 100\mu A, V_{GS} = 0V$	20	-	-	V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS} = 20V, V_{GS} = 0V$	-	-	1	$\mu A$
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 8V, V_{DS} = 0V$	-	-	$\pm 10$	$\mu A$
Gate Threshold Voltage	$V_{GS(off)}$	$I_D = 250\mu A, V_{DS} = V_{GS}$	0.4	0.8	1.3	V
Drain-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 100mA$	-	0.76	1.3	$\Omega$
		$V_{GS} = 2.5V, I_D = 100mA$	-	1.2	1.8	$\Omega$
		$V_{GS} = 1.8V, I_D = 10mA$	-	1.8	3.3	$\Omega$
Input Capacitance	$C_{iss}$	$V_{DS} = 10V, V_{GS} = 0V$ $f = 1MHz$	-	18	-	pF
Output Capacitance	$C_{oss}$		-	5	-	pF
Reverse Transfer Capacitance	$C_{rss}$		-	3	-	pF
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 10V, I_D = 100mA$ $V_{GS} = 4.5V$	-	11	-	ns
Rise Time	$t_r$		-	11	-	ns
Turn-off Delay Time	$t_{d(off)}$		-	45	-	ns
Fall Time	$t_f$		-	32	-	ns
Total Gate Charge	$Q_g$	$V_{DS} = 10V, I_D = 100mA$ $V_{GS} = 6V$	-	0.34	-	nC
Gate-Source Charge	$Q_{gs}$		-	0.03	-	nC
Gate-Drain Charge	$Q_{gd}$		-	0.13	-	nC
Diode Forward Voltage	$V_{SD}$	$I_S = 100mA, V_{GS} = 0V$	-	0.77	1.2	V

## ■ NOTES ON USE

1. Please use this IC within the absolute maximum ratings.

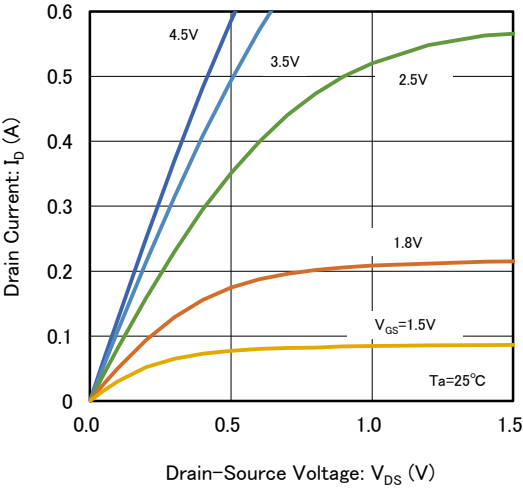
Even within the ratings, in case of high load use continuously such as high temperature, high voltage, high current and thermal stress may cause reliability degradation of the IC.

2. Torex places an importance on improving our products and their reliability.

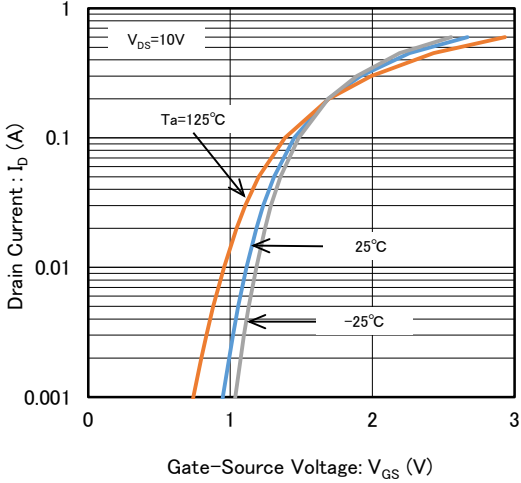
We request that users incorporate fail-safe designs and post-aging protection treatment when using Torex products in their systems.

# TYPICAL PERFORMANCE CHARACTERISTICS

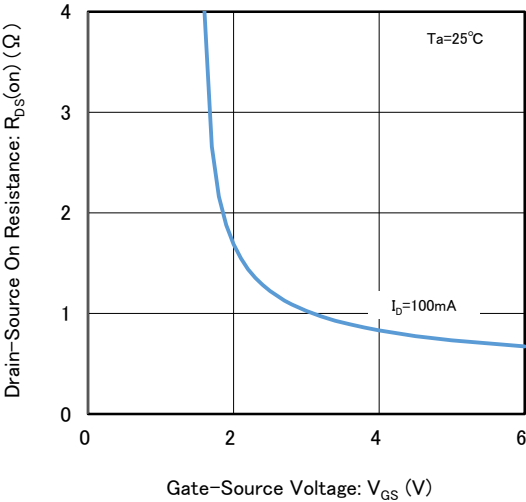
(1) Drain Current vs. Drain-Source Voltage



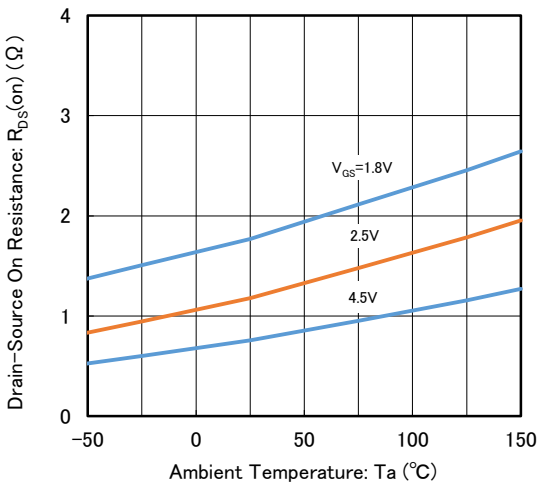
(2) Drain Current vs. Gate-Source Voltage



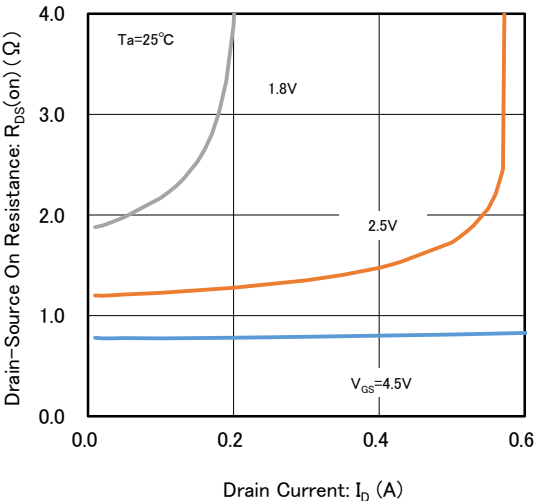
(3) Drain-Source On Resistance vs. Gate-Source Voltage



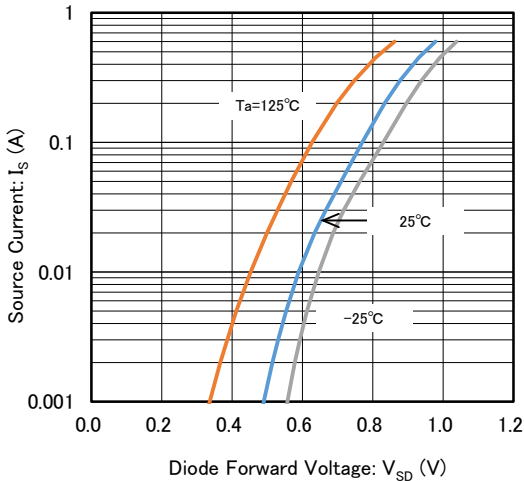
(4) Drain-Source On Resistance vs. Ambient Temperature



(5) Drain-Source On Resistance vs. Drain Current

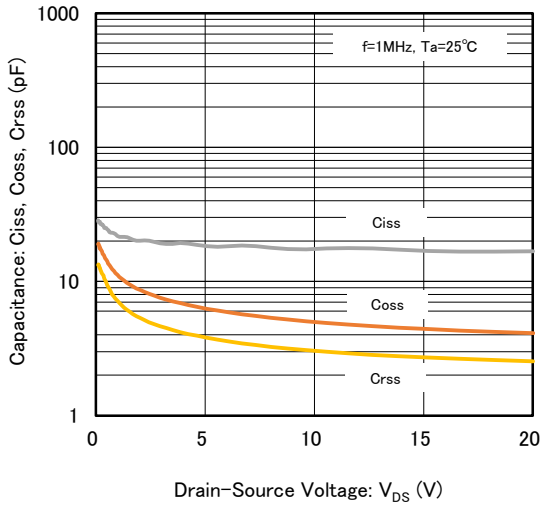


(6) Source Current vs. Diode Forward Voltage

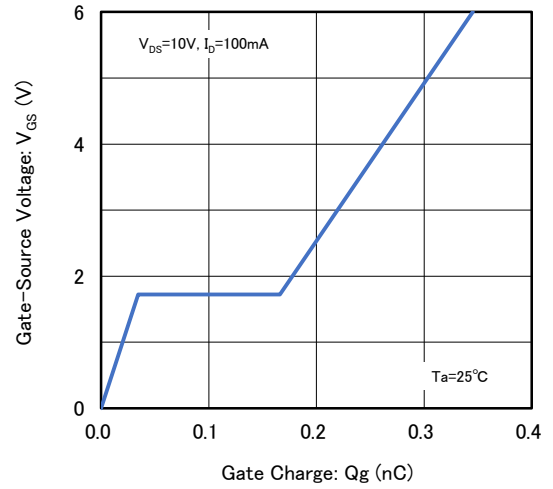


## TYPICAL PERFORMANCE CHARACTERISTICS

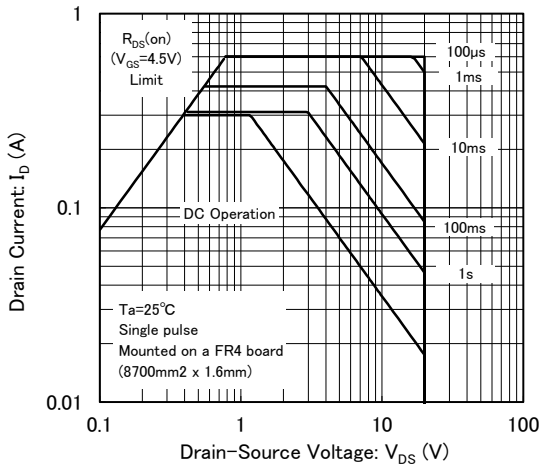
(7) Ciss, Coss, Crss vs. Drain-Source Voltage



(8) Gate-Source Voltage vs. Gate Charge



(9) Area of Safe Operation



## ■ PACKAGING INFORMATION

For the latest package information go to, [www.torexsemi.com/technical-support/packages](http://www.torexsemi.com/technical-support/packages)

PACKAGE	OUTLINE / LAND PATTERN	THERMAL CHARACTERISTICS	
SOT-523	<a href="#">SOT-523 PKG</a>	JESD51-7 Board	<a href="#">SOT-523 Power Dissipation</a>

## ■ MARKING RULE

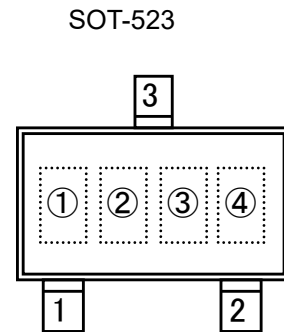
### ● SOT-523

①,② represents product series

MARK		PRODUCT SERIES
①	②	
2	2	XP222N0301**-G

③,④ e presents production lot number

01 to 09, 0A to 0Z, 11 to 9Z, A1 to A9, AA to AZ, B1 to ZZ repeated  
(G, I, J, O, Q, W excluded) \*No character inversion used



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